



BC846BLP4

### 65V NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

### **Features**

- Low Collector-Emitter Saturation Voltage, VCE(SAT)
- Ultra-Small Leadless Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 **e4**
- Weight: 0.0009 grams (Approximate)

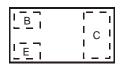
#### X2-DFN1006-3







Device Symbol



Top View Device Schematic

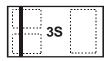
## **Ordering Information** (Note 4)

Part Number	Marking	Reel Size (in)	Tape Width (mm)	Quantity per Reel
BC846BLP4-7B	3S	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



Top View Bar Denotes Base and Emitter Side

3S = Product Type Marking Code

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# **Maximum Ratings** $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	65	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current - Continuous	I <sub>C</sub>	100	mA
Peak Collector Current	I <sub>CM</sub>	200	mA
Peak Emitter Current	I <sub>EM</sub>	200	mA

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	0.46	W	
Power Dissipation	(Note 6)	P <sub>D</sub>	1		
Thermal Resistance, Junction to Ambient	(Note 5)	В	272	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	120	C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	110	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

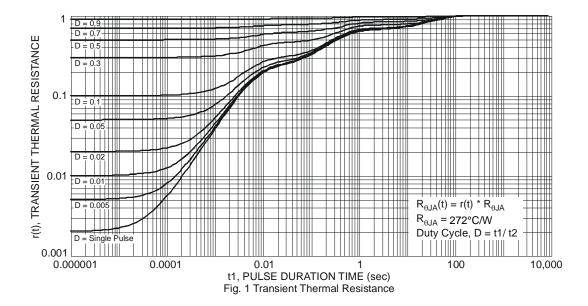
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	200	V	В

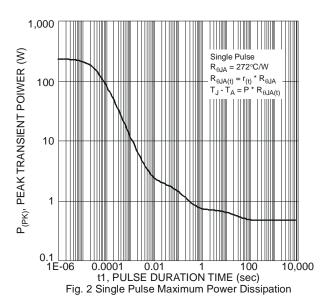
Notes:

- 5. For a device surface mounted on minimum recommended pad layout FR-4 PCB with single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Same as Note 5, except device is surface mounted on 25mm X 25mm collector pad heatsink with 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics**





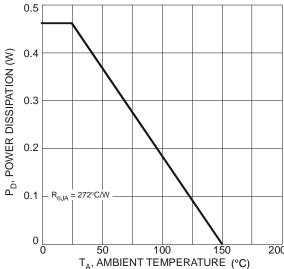


Fig. 3 Power Dissipation vs. Ambient Temperature

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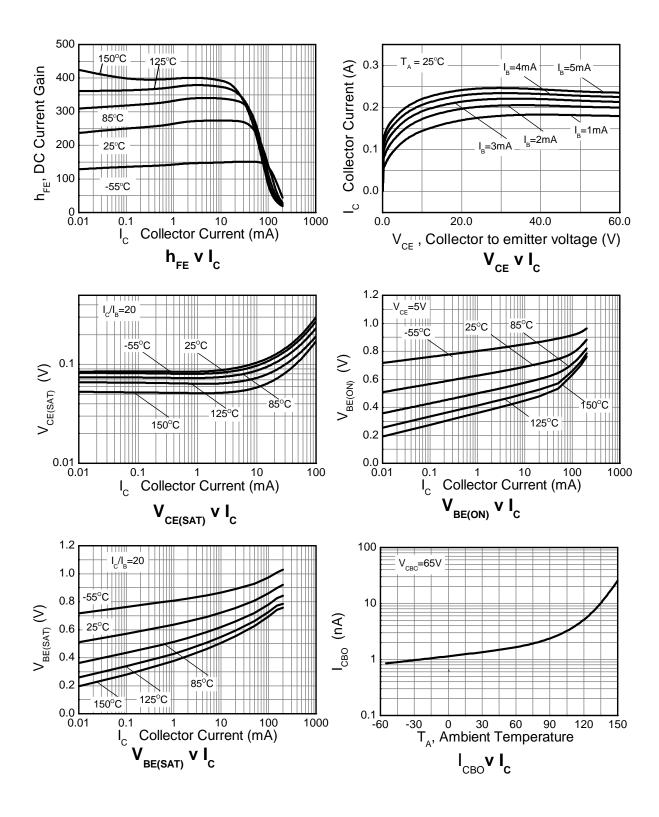
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	80	_	_	V	$I_C = 100\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	65	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	_	_	V	$I_E = 100\mu A, I_C = 0$
Collector Cutoff Current	I <sub>CES</sub>	_	_	15	nA	V <sub>CE</sub> = 65V
Collector Cutoff Current	1		_	15	nA	V <sub>CB</sub> = 40V
	I <sub>CBO</sub>			5.0	μΑ	$V_{CB} = 30V, T_A = +150^{\circ}C$
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h <sub>FE</sub>	200	270	450	—	$V_{CE} = 5V, I_{C} = 2.0mA$
Collector-Emitter Saturation Voltage	Variant		90	250	mV	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	220	600	IIIV	$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	720	900	mV	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$
Dase Emilier Galdration Voltage			870	—		$I_C = 100 \text{mA}, I_B = 5.0 \text{mA}$
Base-Emitter Voltage	V <sub>BE(ON)</sub>	580 —	650	700 770 mV	m\/	$V_{CE} = 5V$ , $I_C = 2.0mA$
			_		IIIV	$V_{CE} = 5V$ , $I_C = 10mA$
SMALL SIGNAL CHARACTERISTICS (Note 9)	SMALL SIGNAL CHARACTERISTICS (Note 9)					
Input Capacitance	C <sub>ibo</sub>	_	6.7	_	pF	$V_{CB} = 5V$ , $f = 1.0MHz$
Output Capacitance	C <sub>obo</sub>	_	1.76	_	pF	$V_{CB} = 10V, f = 1.0MHz$
Current Gain-Bandwidth Product	f⊤	100	300	_	MHz	$V_{CE} = 5V, I_{C} = 10mA, f = 100MHz$
Noise Figure	NF		2	10	dB	$V_{CE} = 5V$ , $I_{C} = 200\mu A$ , $R_{S} = 2.0k\Omega$ , $f = 1.0kHz$ , $\Delta f = 200Hz$
Delay Time	t <sub>D</sub>	_	11.2	_	ns	
Rise Time	t <sub>R</sub>	_	59.7	_	ns	$V_{CC} = 30V$ ,
Storage Time	ts	_	190.8	_	ns	Ic = 150mA,
Fall Time	t <sub>F</sub>	_	108.6	_	ns	$I_{B1} = -I_{B2} = 15 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

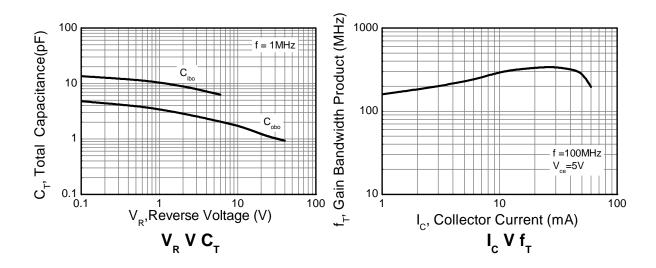


## **Typical Electrical Characteristics**





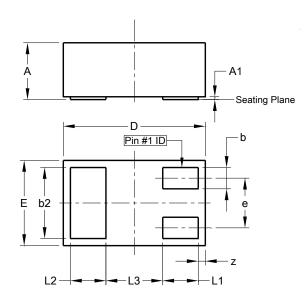
# Typical Electrical Characteristics (Cont.)



# Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

### X2-DFN1006-3



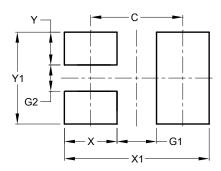
X2-DFN1006-3					
Dim	Min	Max	Тур		
Α	_	0.40	_		
A1	0.00	0.05	0.03		
b	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Е	0.55	0.65	0.60		
e	1	1	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3	-	-	0.40		
Z	0.02	0.08	0.05		
All Dimensions in mm					



### Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-DFN1006-3



Dimensions	Value (in mm)
С	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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